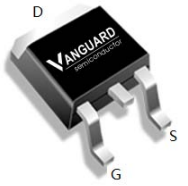
Features

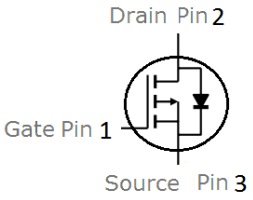
- P-Channel，-5V Logic Level Control
- Fast Switching
- Enhancement mode
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

V_{DS}	-100	V
$R_{DS(on),TYP}$@ V_{GS}=-10 V	243	mΩ
$R_{DS(on),TYP}$@ V_{GS}=-4.5V	257	mΩ
I_D	-10	A

TO-252



Pb-Free RoHS Halogen-Free



Part ID	Package Type	Marking	Tape and reel information
VSD260P10MS	TO-252	260P10M	2500PCS/Reel

Maximum ratings, at T_j =25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		-100	V
I_S	Diode continuous forward current	T_C=25°C	-10	A
I_D	Continuous drain current @V_{GS}=-10V	T_C=25°C	-10	A
		T_C=100°C	-7.3	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	-40	A
EAS	Avalanche energy, single pulsed ②		20	mJ
P_D	Maximum power dissipation	T_C=25°C	48	W
V_{GS}	Gate-Source voltage		±20	V
T_{STG} T_J	Storage and operating temperature range		-55 to 175	°C
Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance-Junction to Case		3.15	°C/W
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		100	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-100V,V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(Tj=125℃)	V_{DS}=-100V,V_{GS}=0V	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1.7	-2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance ③	V_{GS}=-10V, I_D=-10A	--	46	60	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance ③	V_{GS}=-4.5V, I_D=-8A	--	48	70	mΩ
Dynamic Electrical Characteristics @ T_J= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=-25V,V_{GS}=0V, f=1MHz	--	3300	--	pF
C_{oss}	Output Capacitance		--	93	--	pF
C_{rss}	Reverse Transfer Capacitance		--	39	--	pF
Q_g	Total Gate Charge	V_{DS}=-50V,I_D=-2A, V_{GS}=-10V	--	76	--	nC
Q_{gs}	Gate-Source Charge		--	7.4	--	nC
Q_{gd}	Gate-Drain Charge		--	16	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-50V, I_D=-2A, R_G=9.1Ω, V_{GS}=-10V	--	5	--	nS
t_r	Turn-on Rise Time		--	31	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	16	--	nS
t_f	Turn-Off Fall Time		--	22	--	nS
Source- Drain Diode Characteristics@ T_J= 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=-2A,V_{GS}=0V	--	-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=-2A, V_{GS}=0V di/dt=-100A/μs	--	35	--	nS
Q_{rr}	Reverse Recovery Charge			55		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

②Limited by TJmax, starting TJ = 25°C, L = 0.5mH,RG = 25Ω, IAS = -7A, VGS =-10V. Part not recommended for use above this value

③Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics	Figure 2. Transfer Characteristics

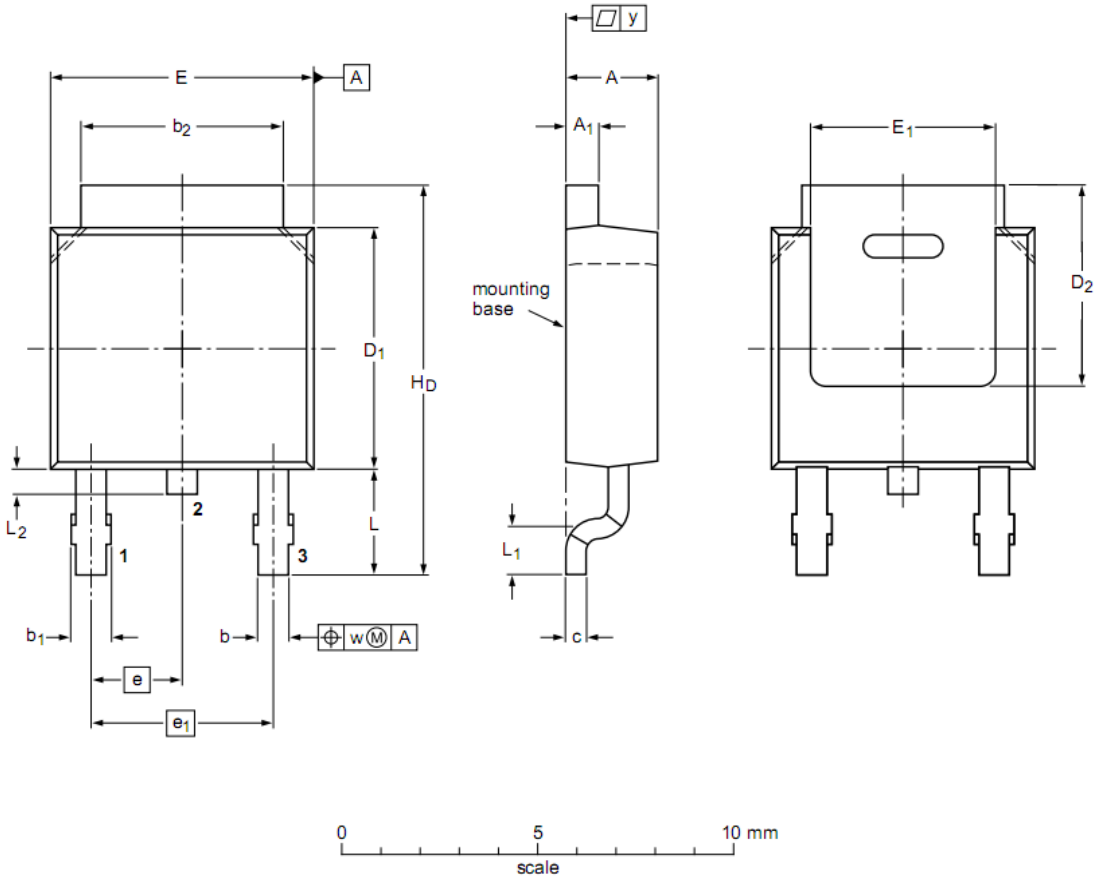
Figure 3. Power Dissipation	Figure 4. Drain Current

Figure 5. BV_{DSS} vs Junction Temperature	Figure 6. $R_{DS(ON)}$ vs Junction Temperature

Figure 7. Gate Charge Waveforms	Figure 8. Capacitance

Figure 9. Body-Diode Characteristics	Figure 10. Maximum Safe Operating Area

TO-252 Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	2.20	2.30	2.38
A_1	0.46	0.50	0.63
b	0.64	0.76	0.89
b_1	0.77	0.85	1.14
b_2	5.00	5.33	5.46
c	0.458	0.508	0.558
D_1	5.98	6.10	6.223
D_2	5.21	--	--
E	6.40	6.60	6.731
E_1	4.40	--	--
e	2.286 BSC		
e_1	--	4.57	--
H_D	9.40	10.00	10.40
L	2.743 REF		
L_1	1.40	1.52	1.77
L_2	0.50	0.80	1.01
w	--	0.20	--
y	--	--	0.20

Notes:

1. Refer to JEDEC TO-252 variation AA
2. Dimension "E" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.1524mm per side.
3. Dimension "D1" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.1524mm per end.